Dual N-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

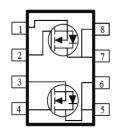
Typical Applications:

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY			
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
20	7 @ V _{GS} = 4.5V	50 ^c	
20	9 @ V _{GS} = 2.5V	50 ^c	

DFN5X6-8L





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			20	V		
Gate-Source Voltage			±12	v		
	T _A =25°C	I_	16 ^a			
Continuous Drain Current	T _A =70°C	I _D	13 ^a	A		
Continuous Drain Current	T _C =25°C		50 [°]			
	T _C =70°C	Ι _D	50 ^c			
Pulsed Drain Current ^b	I _{DM}	80	1			
Continuous Source Current (Diode Conduction) ^a		I _S	4.3			
	T _A =25°C		2.5 ^a			
Power Dissipation	T _A =70°C	P _D	1.6 ^a	W		
	T _C =25°C	ГD	36			
	T _C =70°C		23			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	R _{eja}	50	°C/W			
	Steady State	ιν _θ ja	70				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	3.5				

Notes

- a. Surface Mounted on 1" x 1" FR4 Board
- b. Pulse width limited by maximum junction temperature
- c. Package limited

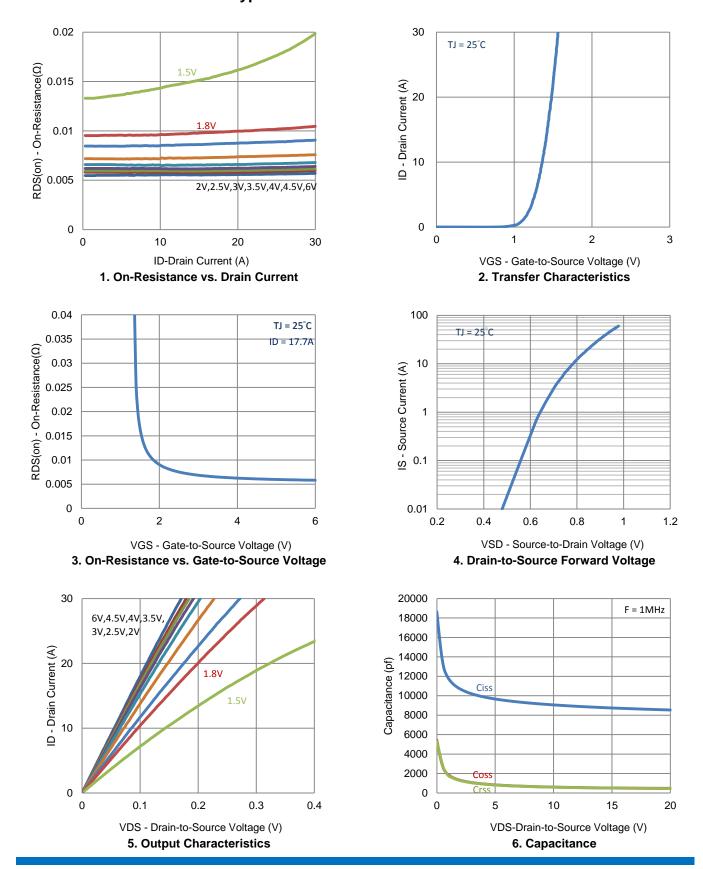
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
Static									
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.4			V			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			±100	nA			
Zero Gate Voltage Drain Current		$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		1		uA			
	IDSS	$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$	5°C		10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	30			А			
Drain Course On Desistance a	r	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 17.7 \text{ A}$			7	m0			
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 14.2 \text{ A}$			9	mΩ			
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 17.7 \text{ A}$		12		S			
Diode Forward Voltage ^a	V_{SD}	$I_{\rm S} = 2.2$ A, $V_{\rm GS} = 0$ V		0.68		V			
	Dynamic ^b								
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		73		nC			
Gate-Source Charge	Q _{gs}	$v_{DS} = 10$ v, $v_{GS} = 4.3$ v, $I_{D} = 17.7$ A		7.8					
Gate-Drain Charge	Q_gd	$I_D = 17.7$ A		17					
Turn-On Delay Time	t _{d(on)}	V 10V B -060		16					
Rise Time	t _r	$V_{DS} = 10 \text{ V}, \text{ R}_{L} = 0.6 \Omega,$ $I_{D} = 17.7 \text{ A},$		36		ns			
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{GEN}} = 1 \Omega$		169					
Fall Time	t _f	V GEN - 7.5 V, INGEN - 1 22		36					
Input Capacitance	C _{iss}			8742					
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		511		рF			
Reverse Transfer Capacitance	C _{rss}			498					

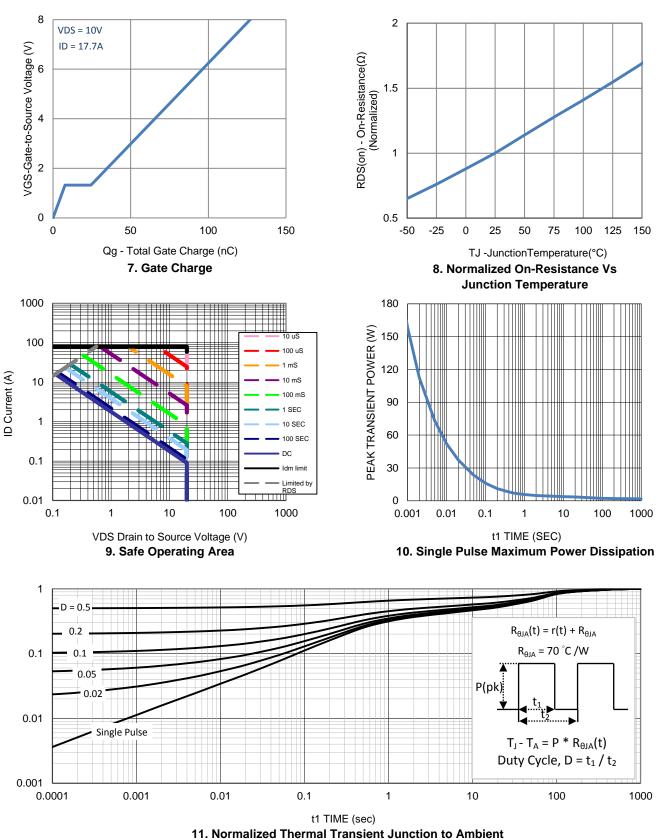
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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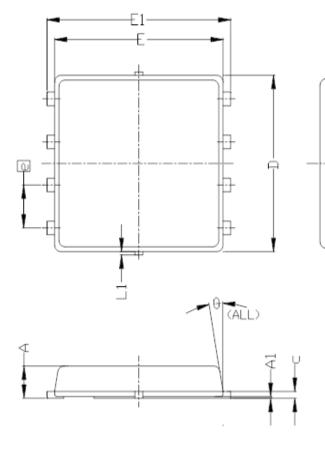


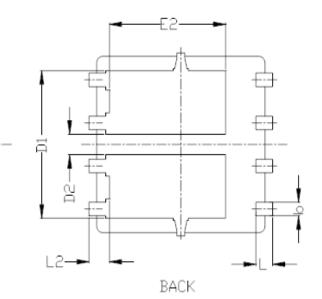
Typical Electrical Characteristics



Typical Electrical Characteristics

Package Information





en moi e	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	5.20 BSC			0.205 BSC			
D1	4.35 BSC			0.171 BSC			
E	5.55 BSC			0.219 BSC			
E1	6.05 BSC			0.238 BSC			
E2	3.62 BSC			0. 143 BSC			
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	